

ALTERNATIVE TO PTO/SB/08A/B  
(Based on PTO 08-08 version)

Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/537,804
				Filing Date	June 7, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	1792
Examiner Name	F. C. Hiteshew				
Sheet	1	of	3	Attorney Docket Number	204552035400

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1.	US-6,177,292-B1	01-23-2001	Hong et al.	
	2.	US-6,248,607-B1	06-19-2001	Tsutsui	
	3.	US-6,355,497-B1	03-12-2002	Romano et al.	
	4.	US-6,475,277-B1	11-05-2002	Hirota et al.	
	5.	US-2002/0192507-A1	12-19-2002	Dwilinski et al.	
	6.	US-6,627,552-B1	09-30-2003	Nishio et al.	
	7.	US-6,639,925-B2	10-28-2003	Niwa et al.	
	8.	US-6,653,663-B2	11-25-2003	Ishida	
	9.	US-6,686,608-B1	02-03-2004	Takahira	
	10.	US-6,693,935-B2	02-17-2004	Tojo et al.	
	11.	US-2004/0089221-A1	05-13-2004	Dwilinski et al.	
	12.	US-6,749,819-B2	06-15-2004	Otsuka et al.	
	13.	US-2004/0238810-A1	12-02-2004	Dwilinski et al.	
	14.	US-2004/0251471-A1	12-16-2004	Dwilinski et al.	
	15.	US-2004/0261692-A1	12-30-2004	Dwilinski et al.	
	16.	US-2005/0087124-A1	04-28-2005	Dwilinski et al.	
	17.	US-2005/0249255-A1	11-10-2005	Dwilinski et al.	
	18.	US-2006/0054075-A1	03-16-2006	Dwilinski et al.	
	19.	US-2006/0054076-A1	03-16-2006	Dwilinski et al.	
	20.	US-2006/0057749-A1	03-16-2006	Dwilinski et al.	
	21.	US-2006/0124051-A1	06-15-2006	Yoshioka et al.	
	22.	US-2006/0138431-A1	06-29-2006	Dwilinski et al.	
	23.	US-7,252,712-B1	08-07-2007	Dwilinski et al.	
	24.	US-7,314,517-B2	01-01-2008	Dwilinski et al.	
	25.	US-7,315,599-B2	01-01-2008	Morriss	
	26.	US-7,335,262-B2	02-26-2008	Dwilinski et al.	
	27.	US-2008/0050855-A1	02-28-2008	Dwilinski et al.	
	28.	US-7,364,619-B2	04-29-2008	Dwilinski et al.	
	29.	US-2008/0108162-A1	05-08-2008	Dwilinski et al.	
	30.	US-7,374,615-B2	05-20-2008	Dwilinski et al.	
	31.	US-7,387,677-B2	06-17-2008	Dwilinski et al.	
	32.	US-2008/0156254-A1	07-03-2008	Dwilinski et al.	
	33.	US-7,420,261-B2	09-02-2008	Dwilinski et al.	
	34.	US-7,422,633-B2	09-09-2008	Dwilinski et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
	35.	JP-51-41686	04-08-1976	Matsushita Electric Industrial Co., Ltd.	Translation of abstract	
	36.	WO-94/28204	12-08-1994	Technalum Research, Inc.		
	37.	WO-97/13891	04-17-1997	Centrum Badan Wysokocisnieniowych		
	38.	JP-9-508093	08-19-1997		Corresponds to WO-94/28204 listed above	

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				Examiner Name	F. C. Hiteshew
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	39.	JP-2000-327495	11-28-2000	Japan Science and Technology Corp.		✓
	40.	JP-2001-077038	03-23-2001	Sumitomo Electric Industries	Translation of abstract and corresponds to US-6,475,277 listed above	
	41.	EP-1 164 210-A2	12-19-2001	Sharp Kabushiki Kaisha		
	42.	JP-2002-026442	01-25-2002	Sony Corp.	Translation of abstract	
	43.	PL-347918	12-16-2002	Ammono SP.Zo.o; Nichia Corporation		✓
	44.	WO-02/101124-A1	12-19-2002	Nichia Corporation	Translation of abstract	
	45.	PL-350375	05-05-2003	Ammono SP.Zo.o; Nichia Corporation		✓
	46.	EP-1 405 936-A1	04-07-2004	Ammono SP. Zo.o		
	47.	WO-2004/090202-A1	10-21-2004	Mitsubishi Chemical Corporation; Tokyo Denpa Co., Ltd.	Translation of abstract	
	48.	EP-1 616 981-A1	01-18-2006	Tokyo Denpa Co., Ltd.; Mitsubishi Chemical Corporation		
	49.	CN-1260409	06-21-2006	Ammono SP. ZO.O	Translation of abstract and corresponds to WO-02/101124 listed above	

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NON PATENT LITERATURE DOCUMENTS				
Examine r Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
	50.	Supplementary European Search Report, dated September 23, 2008, European Patent Application No.02788783.5; 3 pages		
	51.	Chinese Office Action, dated July 18, 2008, directed to Chinese Patent Application No. 200580040008.X; 25 pages		✓
	52.	Chinese Office Action, dated December 28, 2007, directed to Chinese Patent Application No. 02802023.5; 8 pages		✓
	53.	Japanese Notification, mailed March 14, 2006, directed to Japanese Patent Application No. 2003-50367; 3 pages		✓
	54.	Japanese Notification of Reason(s) for Refusal, mailed December 16, 2008, directed to Japanese Patent Application No. 2004-505416; 7 pages		✓
	55.	Japanese Notification of Reason(s) for Refusal, mailed January 6, 2009, directed to Japanese Patent Application No. 2004-506101; 7 pages		✓

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56.	International Search Report, mailed May 7, 2004, directed to International Patent Application No. PCT/JP03/15906; 3 pages	
57.	International Search Report, mailed September 29, 2005, directed to International Patent Application No. PCT/JP2005/011091; 3 pages	
58.	International Search Report, mailed April 21, 2006, directed to International Patent Application No. PCT/JP2005/022396; 3 pages	
59.	U.S. Office Action, mailed October 16, 2007, directed to U.S. Patent Application No. 10/538,654; 10 pages	
60.	U.S. Office Action, mailed April 2, 2007, directed to U.S. Patent Application No. 10/538,407; 13 pages	
61.	Song, Y. et al. (2003). "Bulk GaN Single Crystals: Growth Conditions by Flux Method." <i>Journal of Crystal Growth</i> . 247:275-278	
62.	Beaumont, B. et al. (2001). "Epitaxial Lateral Overgrowth of GaN." <i>Phys. Stat. Sol.(b)</i> . 227(1); 1-43	
63.	Liu, L. et al. (2002). "Substrates for Gallium Nitride Epitaxy." <i>Reports: A Review Journal, Materials Science and Engineering</i> . 37:61-127	
64.	Yano, M. et al. (2000). "Growth of Nitride Crystals, BN, AlN and GaN by Using a Na Flux" <i>Diamond and Related Materials</i> . 9:512-515	
65.	Yamane, H. et al. (July 1, 1998). "Na Flux Growth of GaN Single Crystals" <i>Journal of the Japanese Association for Crystal Growth</i> . 25(4):14-18	
66.	Yamane, H. et al. (1998). "Morphology and Characterization of GaN Single Crystals Grown in a Na Flux." <i>Journal of Crystal Growth</i> . 186:8-12	
67.	Purdy, A. "Ammonothermal Synthesis of Cubic Gallium Nitride." <i>American Chemical Society. Chem. Mater.</i> 11(7):1648-1651	
68.	Sangwal, K. (1994). "Growth Apparatus." Chapter 10.3 In <i>Elementary Crystal Growth</i> . Lublin:331	
69.	Ikornikova, N. IO. (1975). "Hydrothermal Synthesis of Crystals in Chloride Systems," <i>Izd. Nauka, ed. Moscow</i> : 124-125; 132-133	✓
70.	Lan, Y.C. et al., (April 14, 2000). "Syntheses and Structure of Nanocrystalline Gallium Nitride Obtained from Ammonothermal Method Using Lithium Metal as Mineralizer," <i>Materials Research Bulletin</i> 35:2325-2330.	
71.	Polish Patent Office Notification and Search Report, dated January 15, 2007, directed to Polish Patent Application No. P-347918/DP. 8 pages	✓
72.	Penkala, T., (1972). "Zarys Krystalografii (Basics of Crystallography)". PWN, Warszawa: 349	✓

Examiner Signature	/Felisa Hiteshew/	Date Considered	06/05/2009
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\*Applicant's unique citation designation number (optional). \*Applicant is to place a check mark here if English language Translation is attached.